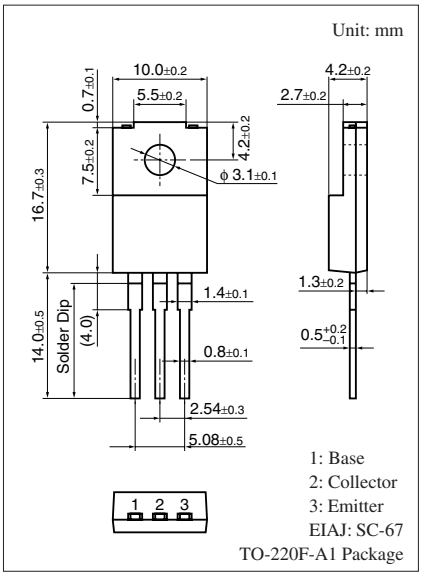
2SD1263, 2SD1263A

Silicon NPN triple diffusion planar type

For power amplification



■ Features

- High collector-base voltage (Emitter open) V_{CBO}
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings $T_a = 25°C$

Parameter		Symbol	Rating	Unit
Collector-base voltage (Emitter open)	2SD1263	V_{CBO}	350	V
	2SD1263A		400	
Collector-emitter voltage (Base open)	2SD1263	V_{CEO}	250	V
	2SD1263A		300	
Emitter-base voltage (Collector open)		V_{EBO}	5	V
Collector current		I_C	0.75	A
Peak collector current		I_{CP}	1.5	A
Collector power dissipation	$T_C = 25°C$	P_C	35	W
			2.0	
Junction temperature		T_j	150	°C
Storage temperature		T_{stg}	−55 to +150	°C

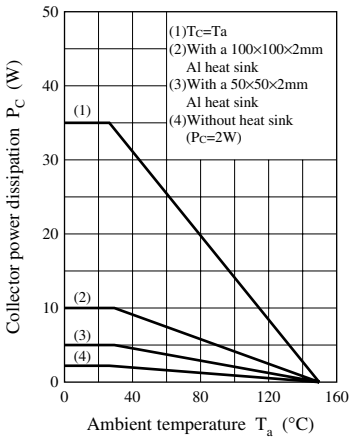
■ Electrical Characteristics $T_a = 25°C \pm 3°C$

Parameter		Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	2SD1263	V_{CEO}	I_C = 30 mA, I_B = 0	250			V
	2SD1263A			300			
Base-emitter voltage		V_{BE}	V_{CE} = 10 V, I_C = 1 A			1.5	V
Collector-emitter cutoff current (E-B short)	2SD1263	I_{CES}	V_{CE} = 350 V, V_{BE} = 0			1	mA
	2SD1263A		V_{CE} = 400 V, V_{BE} = 0			1	
Collector-emitter cutoff current (Base open)	2SD1263	I_{CEO}	V_{CE} = 150 V, I_B = 0			1	mA
	2SD1263A		V_{CE} = 200 V, I_B = 0			1	
Emitter-base cutoff current (Collector open)		I_{EBO}	V_{EB} = 5 V, I_C = 0			1	mA
Forward current transfer ratio		h_{FE1} *	V_{CE} = 10 V, I_C = 0.3 A	40		250	—
		h_{FE2}	V_{CE} = 10 V, I_C = 1 A	10			
Collector-emitter saturation voltage		$V_{CE(sat)}$	I_C = 1 A, I_B = 0.2 A			1	V
Transition frequency		f_T	V_{CE} = 5 V, I_C = 0.5 A, f = 10 MHz		30		MHz
Turn-on time		t_{on}	I_C = 1 A, I_{B1} = 0.1 A, I_{B2} = − 0.1 A		0.5		µs
Storage time		t_{stg}	V_{CC} = 50 V		2.0		µs
Fall time		t_f			0.5		µs

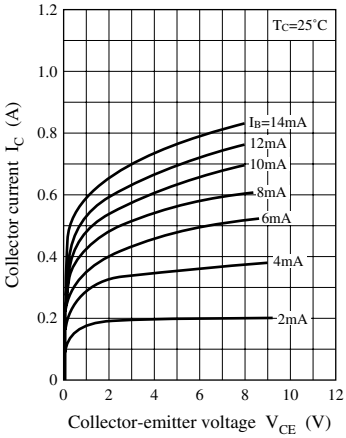
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.
2. *: Rank classification

Rank	R	Q	P
h_{FE1}	40 to 90	70 to 150	120 to 250

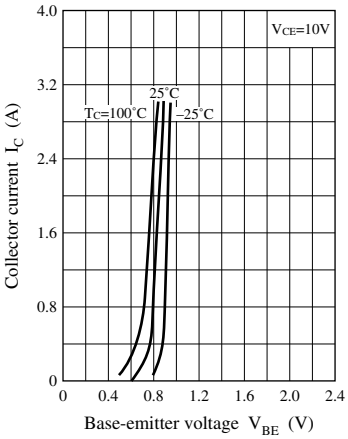
P_C — T_a



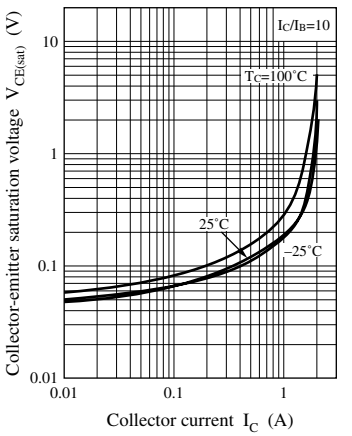
I_C — V_{CE}



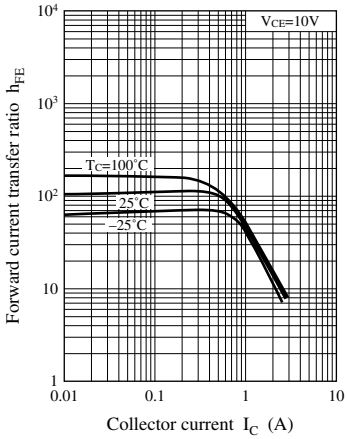
I_C — V_{BE}



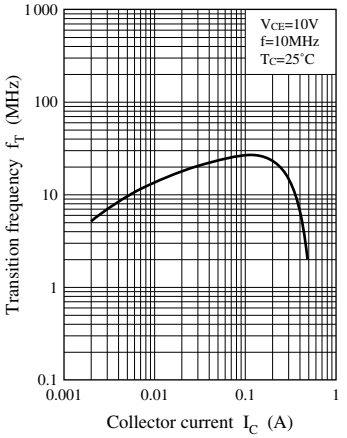
$V_{CE(sat)}$ — I_C



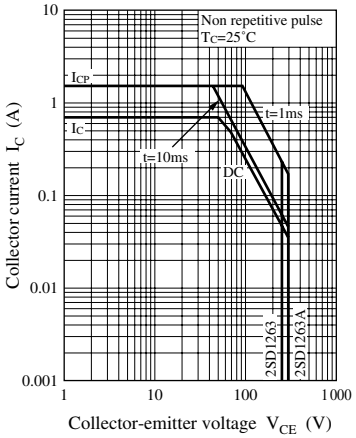
h_{FE} — I_C



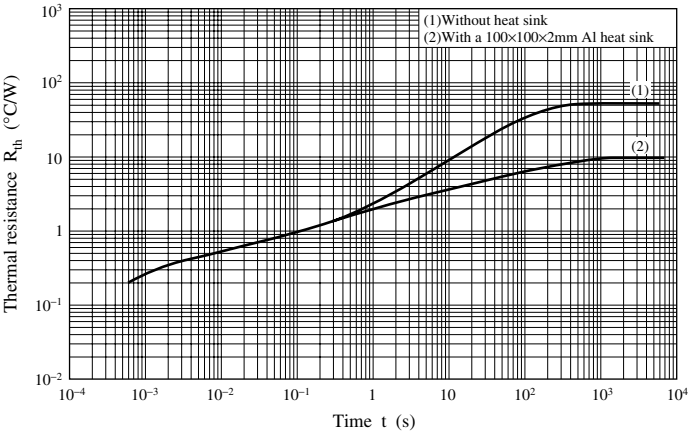
f_T — I_C



Safe operation area



R_{th} — t



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